

WHAT IS CLAIMED IS:

1. A deposition mask for placing between a depositing material and a medium on which deposition is performed, including
5 a pattern for allowing said depositing material to be selectively attached to a desired position on said medium, wherein
said mask is composed of a semiconductor substrate.

2. A deposition mask as defined in Claim 1, wherein
10 said semiconductor substrate is composed of silicon.

3. A deposition mask for placing between a depositing material and a medium on which deposition is performed, comprising:
a semiconductor substrate including an opening forming
15 region having a reduced thickness provided with at least one opening for allowing said depositing material to be selectively attached to a desired position on said medium, and a thick portion formed in at least one portion of an outer periphery region of said mask.

4. A deposition mask as defined in Claim 3, wherein
20 said semiconductor substrate is composed of silicon.

5. A deposition mask as defined in Claim 3, wherein
said semiconductor substrate is composed of single
25 crystalline or polycrystalline silicon.

6. A method for manufacturing a deposition mask, wherein
said deposition mask for placing between a depositing material and a medium on which deposition is performed comprises

a semiconductor substrate including an opening forming region having a reduced thickness provided with at least one opening for allowing said depositing material to be selectively attached to a desired position on said medium, and a thick portion formed in
5 at least one portion of a mask outer periphery region of said semiconductor substrate,

said method comprising the steps of:

forming a first coating covering a region in which said thick portion of said semiconductor substrate is to be formed ;

10 using said first coating as an etching mask to etch said semiconductor substrate so as to reduce thickness of said semiconductor substrate and thereby form said opening forming region;

forming a second coating in areas other than a predetermined position within said opening forming region; and
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using said second coating as an etching mask to etch said semiconductor substrate so as to form said at least one opening in said predetermined position.

20 7. A deposition mask as defined in Claim 6, wherein said semiconductor substrate is composed of silicon.

8. A deposition mask manufacturing method as defined in Claim 6, wherein

25 said first coating is formed on a first side of said semiconductor substrate;

said opening forming region is formed by etching said first side of said semiconductor substrate to reduce thickness of said substrate;

said second coating is formed on a second side of said semiconductor substrate; and

said at least one opening is formed by etching from said second side until penetrating through said semiconductor substrate.

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9. A method for manufacturing an electroluminescence display device composed by arranging a plurality of display pixels, each display pixel having an electroluminescence element including at least an emissive layer between first and second electrodes, said method comprising the steps of:

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arranging a deposition mask on a medium having said first electrode formed thereon; and

attaching an emissive material from an emissive material source via an opening in said deposition mask to a corresponding display pixel region of said medium, thereby forming an emissive layer for each pixel; wherein

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said deposition mask for placing between a depositing material and said medium on which deposition is performed comprises a semiconductor substrate including an opening forming region having a reduced thickness provided with at least one opening for allowing said depositing material to be selectively attached to a desired position on said medium, and a thick portion formed in at least one portion of a mask outer periphery region of said semiconductor substrate; and

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said deposition mask is obtained through the steps of:

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forming a first coating covering a region in which said thick portion of said semiconductor substrate is to be formed ;

using said first coating as an etching mask to etch said semiconductor substrate so as to reduce thickness of said

semiconductor substrate and thereby form said opening forming region;

forming a second coating in areas other than a predetermined position within said opening forming region; and

5 using said second coating as an etching mask to etch said semiconductor substrate so as to form said at least one opening in said predetermined position.

10 10. A method for manufacturing an electroluminescence display device as defined in Claim 9, wherein

each of said elements includes between said first and second electrodes at least an emissive layer containing an organic material; and

15 said organic material supplied from said emissive material source is attached via said opening of said deposition mask to a corresponding pixel.

11. A method for manufacturing an electroluminescence display device as defined in Claim 9, wherein

20 each of said elements is composed by including between said first and second electrodes at least an emissive layer containing an organic material corresponding to an emitted color; and

said deposition mask having said opening formed only in a region corresponding to a pixel for a predetermined color is used
25 to attach said organic material supplied from said emissive material source to a corresponding pixel region.

12. An electroluminescence display device formed using the manufacturing method defined in Claim 9.

13. A color organic electroluminescence display device formed using the manufacturing method defined in Claim 9.